TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK3497

High Power Amplifier Application

- High breakdown voltage: V_{DSS} = 180 V
- Complementary to 2SJ618

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	180	٧	
Gate-source voltage		V_{GSS}	±12	V	
Drain current	DC (Note 1)	I _D	10	Α	
	Pulse (Note 1)	I _{DP}	30	Α	
Drain power dissipation (Tc = 25°C)		P_{D}	130	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

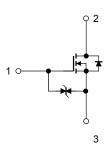
Note 1: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}.$

Weight: 4.6 g (typ.)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	0.96	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W



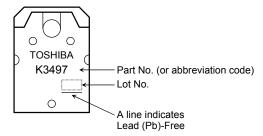
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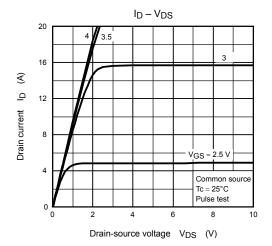
Electrical Characteristics (Ta = 25°C)

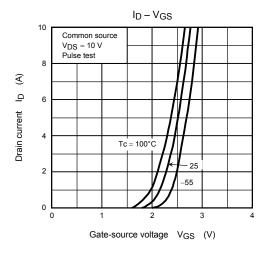
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain cut-off current	I _{DSS}	$V_{DS} = 180V, V_{GS} = 0 V$	_	_	100	μΑ
Gate leakage current	I _{GSS}	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	10	μА
Drain-source breakdown voltage	V (BR) DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	180	_	_	V
Drain-source saturation voltage	V _{DS (ON)}	$V_{GS} = 7 \text{ V}, I_D = 5 \text{ A}$	_	_	0.75	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.1	_	2.1	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$	6.0	12.0	_	S
Input capacitance	C _{iss}		_	2400	_	
Output capacitance	C _{oss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	220	_	pF
Reverse transfer capacitance	C _{rss}		_	30	_	

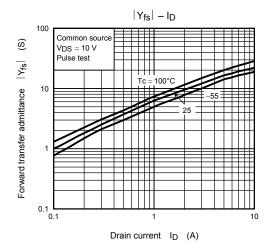
This transistor is an electrostatic-sensitive device. Please handle with caution.

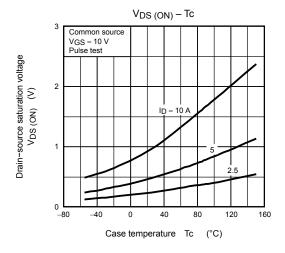
Marking

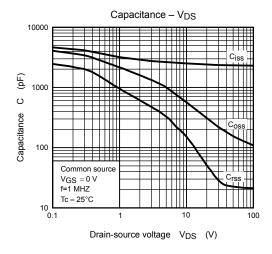


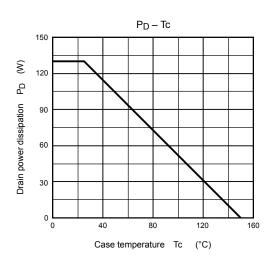




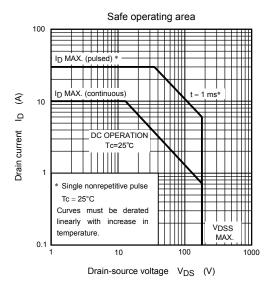








3 2009-01-27



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5 2009-01-27